AnserRF

Internal Matching GaN Power Amplifier Module

ANMI051059-P38

C-band matched GaN power amplifier module

Features:

Frequency: 5.15~5.85GHz Output Power: Pout≥38dBm

. PowerGain: Gain≥18dB Add-Efficiency: PAE≥30% Port Matching: Zin/Zout=50Ω

Description:

ANMI051059-P38 is an internal matching GaN power amplifier module, which adopts advanced co-planar internal matching MCM and thin film circuit technology. The typical working frequency range is 5.15~5.85GHz. This device can be used in different RF/Microwave system and subsystem. The high output power level, high efficiency and wide operating temperature range can make application very flexible.

Maximun Ratings (TC=25°C, Not recommended working under this condition):

	Symbol	Value	Unit
Voltage between source and drain	V _{DS}	40	V
Voltage between gate and source	V _{GS}	-5	V
Storage Temperature Range	T_{stg}	-65 to +175	°C
Drain and Source Channel Temperature	Tch	175	°C

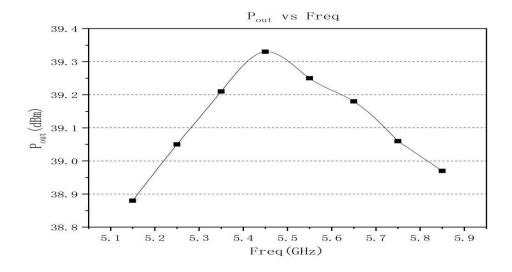


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Electrical Characteristics:

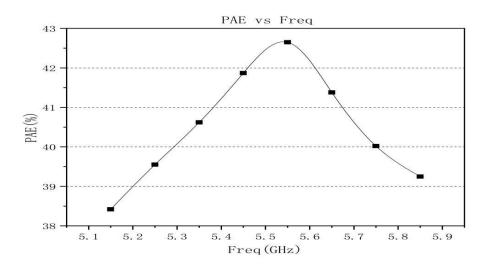
				Value		
	Symbol	Test condition	Min	Тур	Max	Unit
Drain Current	ldsr	Vds=28V CW. Pin: 20dBm Freq: 5.15~5.85GHz	-	0.8	-	Α
Output Power	Pout		38	39	-	dBm
Gain	Gp		18	19	-	dB
Add-Efficiency	PAE		30	35	-	%
Gain Flatness	ΔG		-0.8	-	+0.8	dB

Typical Curve:

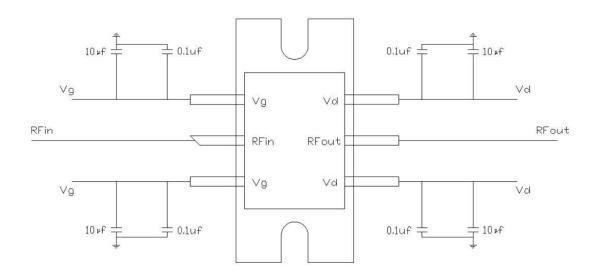




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Application Circuit:



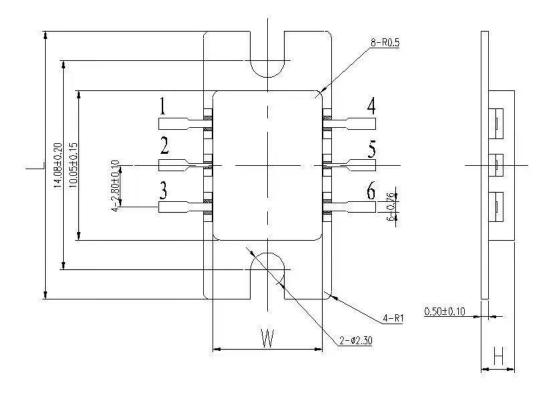


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ESD Level:

ESD	Class III	2000V

Outline:



Precautions for use:

- Pay attention to drying transportation and storage.
- Pay attention to anti-static during chip use and assembly, and wear grounding anti-static bracelet.
- When powering up, first apply grid power then add leakage.